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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Communications; CPM, Security; SEC
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8555epxaqf

1 Overview

The following section provides a high-level overview of the MPC8555E features. Figure 1 shows the major functional units within the MPC8555E.

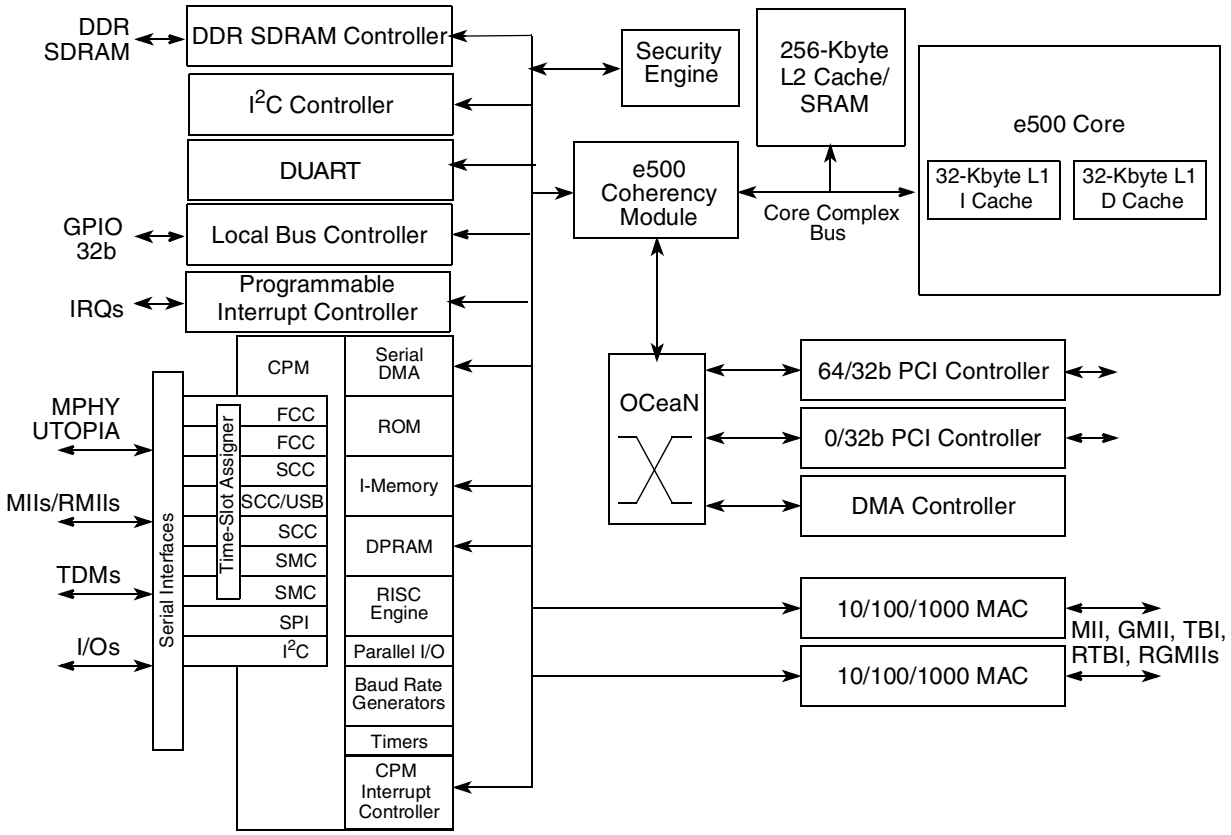

Figure 1. MPC8555E Block Diagram

1.1 Key Features

The following lists an overview of the MPC8555E feature set.

- Embedded e500 Book E-compatible core
  - High-performance, 32-bit Book E-enhanced core that implements the PowerPC architecture
  - Dual-issue superscalar, 7-stage pipeline design
  - 32-Kbyte L1 instruction cache and 32-Kbyte L1 data cache with parity protection
  - Lockable L1 caches—entire cache or on a per-line basis
  - Separate locking for instructions and data
  - Single-precision floating-point operations
  - Memory management unit especially designed for embedded applications
  - Enhanced hardware and software debug support
  - Dynamic power management
  - Performance monitor facility

  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high resolution timers/counters that can generate interrupts
  - Supports additional internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing
  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs
  - Interrupt summary registers allow fast identification of interrupt source
- Two I^2C controllers (one is contained within the CPM, the other is a stand-alone controller which is not part of the CPM)
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the stand-alone I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (RXD, TXD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 166 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
  - Three protocol engines available on a per chip select basis:
    - General purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Two Three-speed (10/100/1000)Ethernet controllers (TSECs)
  - Dual IEEE 802.3, 802.3u, 802.3x, 802.3z AC compliant controllers
  - Support for Ethernet physical interfaces:
    - 10/100/1000 Mbps IEEE 802.3 GMII
    - 10/100 Mbps IEEE 802.3 MII

  - PCI 3.3-V compatible
  - Selectable hardware-enforced coherency
  - Selectable clock source (SYSCLK or independent PCI_CLK)
- Power management
  - Fully static 1.2-V CMOS design with 3.3- and 2.5-V I/O
  - Supports power save modes: doze, nap, and sleep
  - Employs dynamic power management
  - Selectable clock source (sysclk or independent PCI_CLK)
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- IEEE Std 1149.1™-compatible, JTAG boundary scan
- 783 FC-PBGA package

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8555E. The MPC8555E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings [1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
PLL supply voltage		AV_{DD}	–0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
DDR DRAM I/O voltage		GV_{DD}	–0.3 to 3.63	V	
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	
CPM, PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	3
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	CPM, Local bus, DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)1	V	5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Sequencing

The MPC8555Erequires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DDn}
2. GV_{DD}, LV_{DD}, OV_{DD} (I/O supplies)

Table 5. Typical I/O Power Dissipation

Interface	Parameters	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O	CCB = 200 MHz	0.46	—	—	—	W	—
	CCB = 266 MHz	0.59	—	—	—	W	—
	CCB = 300 MHz	0.66	—	—	—	W	—
	CCB = 333 MHz	0.73	—	—	—	W	—
PCI I/O	64b, 66 MHz	—	0.14	—	—	W	—
	64b, 33 MHz	—	0.08	—	—	W	—
	32b, 66 MHz	—	0.07	—	—	W	Multiply by 2 if using two 32b ports
	32b, 33 MHz	—	0.04	—	—	W	
Local Bus I/O	32b, 167 MHz	—	0.30	—	—	W	—
	32b, 133 MHz	—	0.24	—	—	W	—
	32b, 83 MHz	—	0.16	—	—	W	—
	32b, 66 MHz	—	0.13	—	—	W	—
	32b, 33 MHz	—	0.07	—	—	W	—
TSEC I/O	MII	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	0.07	—	W	
	RGMII or RTBI	—	—	—	0.04	W	
CPM - FCC	MII	—	0.015	—	—	W	—
	RMII	—	0.013	—	—	W	—
	HDLC 16 Mbps	—	0.009	—	—	W	—
	UTOPIA-8 SPHY	—	0.06	—	—	W	—
	UTOPIA-8 MPHY	—	0.1	—	—	W	—
	UTOPIA-16 SPHY	—	0.094	—	—	W	—
	UTOPIA-16 MPHY	—	0.135	—	—	W	—
CPM - SCC	HDLC 16 Mbps	—	0.004	—	—	W	—
TDMA or TDMB	Nibble Mode	—	0.01	—	—	W	—
TDMA or TDMB	Per Channel	—	0.005	—	—	W	Up to 4 TDM channels, multiply by number of TDM channels.

4.3 Real Time Clock Timing

Table 8 provides the real time clock (RTC) AC timing specifications.

Table 8. RTC AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
RTC clock high time	t_{RTCH}	2 x t_{CCB_CLK}	—	—	ns	—
RTC clock low time	t_{RTCL}	2 x t_{CCB_CLK}	—	—	ns	—

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the MPC8555E. Table 9 provides the RESET initialization AC timing specifications.

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	µs	—
Minimum assertion time for $\overline{\text{SRESET}}$	512	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before HRESET negation	100	—	µs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Notes:
1. SYSCLK is identical to the PCI_CLK signal and is the primary clock input for the MPC8555E. See the *MPC8555E PowerQUICC™ III Integrated Communications Processor Reference Manual* for more details.

Table 10 provides the PLL and DLL lock times.

Table 10. PLL and DLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	µs	—
DLL lock times	7680	122,880	CCB Clocks	1, 2

Notes:
1. DLL lock times are a function of the ratio between the output clock and the platform (or CCB) clock. A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The CCB clock is determined by the SYSCLK × platform PLL ratio.

Table 18. GMII, MII, and TBI DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}	—		3.13	3.47	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	1.70	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN} [1] = LV_{DD}		—	40	µA
Input low current	I_{IL}	V_{IN} [1] = GND		–600	—	µA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 19. GMII, MII, RGMII RTBI, and TBI DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	2.37	2.63	V
Output high voltage (LV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.00	LV_{DD} + 0.3	V
Output low voltage (LV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND – 0.3	0.40	V
Input high voltage (LV_{DD} = Min)	V_{IH}	1.70	LV_{DD} + 0.3	V
Input low voltage (LV_{DD} = Min)	V_{IL}	–0.3	0.70	V
Input high current (V_{IN} [1] = LV_{DD})	I_{IH}	—	10	µA
Input low current (V_{IN} [1] = GND)	I_{IL}	–15	—	µA

Note:
1. Note that the symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1and Table 2.

8.2.3 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.3.1 MII Transmit AC Timing Specifications

Table 22 provides the MII transmit AC timing specifications.

Table 22. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}[2]	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise and fall time	t_{MTXR}, t_{MTXF} [2,3]	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.
3. Guaranteed by design.

Figure 10 shows the MII transmit AC timing diagram.

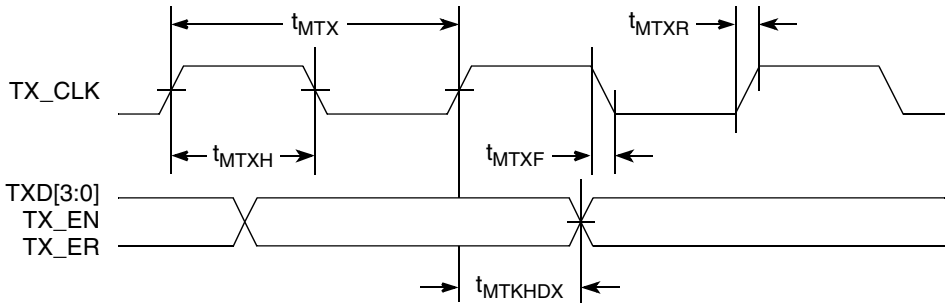

Figure 10. MII Transmit AC Timing Diagram

8.2.3.2 MII Receive AC Timing Specifications

Table 23 provides the MII receive AC timing specifications.

Table 23. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}[2]	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise and fall time	t_{MRXR}, t_{MRXF} [2,3]	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.
3. Guaranteed by design.

Figure 11 shows the MII receive AC timing diagram.

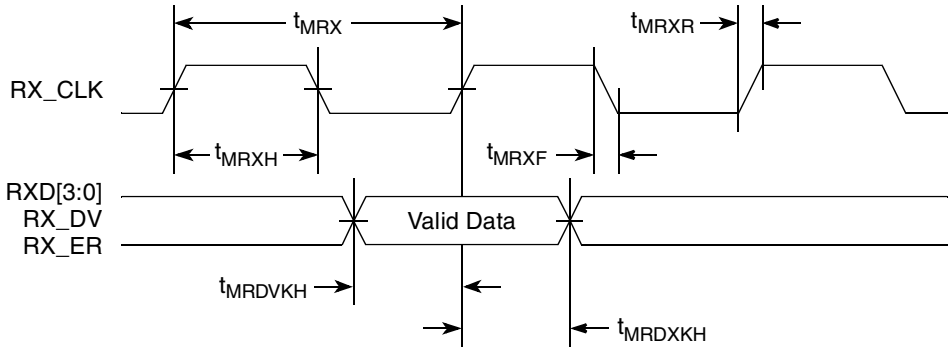

Figure 11. MII Receive AC Timing Diagram

8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

8.2.4.1 TBI Transmit AC Timing Specifications

Table 24 provides the MII transmit AC timing specifications.

Table 24. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%
GMII data TCG[9:0], TX_ER, TX_EN setup time GTX_CLK going high	t_{TTKHDV}	2.0	—	—	ns
GMII data TCG[9:0], TX_ER, TX_EN hold time from GTX_CLK going high	t_{TTKHDX}	1.0	—	—	ns
GTX_CLK clock rise and fall time	t_{TTXR}, t_{TTXF} [2,3]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.
3. Guaranteed by design.

Figure 12 shows the TBI transmit AC timing diagram.

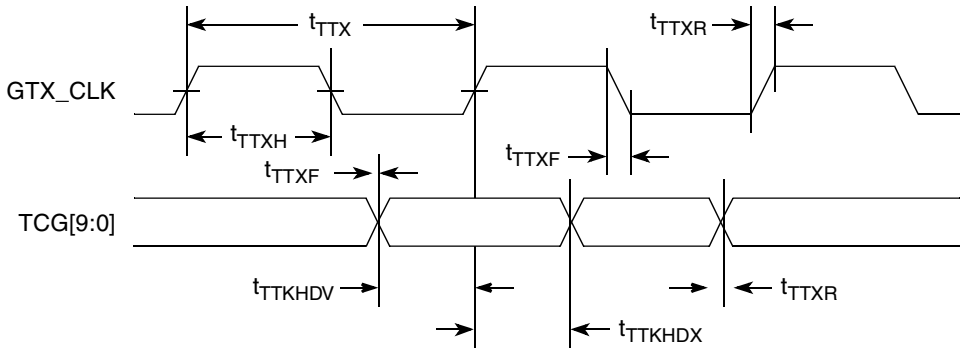

Figure 12. TBI Transmit AC Timing Diagram

Table 27. MII Management DC Electrical Characteristics (continued)

Parameter	Symbol	Conditions		Min	Max	Unit
Input high current	I_{IH}	LV_{DD} = Max	V_{IN} [1] = 2.1 V	—	40	μA
Input low current	I_{IL}	LV_{DD} = Max	V_{IN} = 0.5 V	–600	—	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

8.3.2 MII Management AC Electrical Specifications

Table 28 provides the MII management AC timing specifications.

Table 28. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	0.893	—	10.4	MHz	2
MDC period	t_{MDC}	96	—	1120	ns	
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	
MDC to MDIO valid	t_{MDKHDV}			$2*[1/(f_{ccb\_clk}/8)]$	ns	3
MDC to MDIO delay	t_{MDKHDX}	10	—	$2*[1/(f_{ccb\_clk}/8)]$	ns	3
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	
MDC rise time	t_{MDCR}	—	—	10	ns	
MDC fall time	t_{MDHF}	—	—	10	ns	

Notes:
1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the system clock speed (that is, for a system clock of 267 MHz, the delay is 70 ns and for a system clock of 333 MHz, the delay is 58 ns).
3. This parameter is dependent on the CCB clock speed (that is, for a CCB clock of 267 MHz, the delay is 60 ns and for a CCB clock of 333 MHz, the delay is 48 ns).
4. Guaranteed by design.

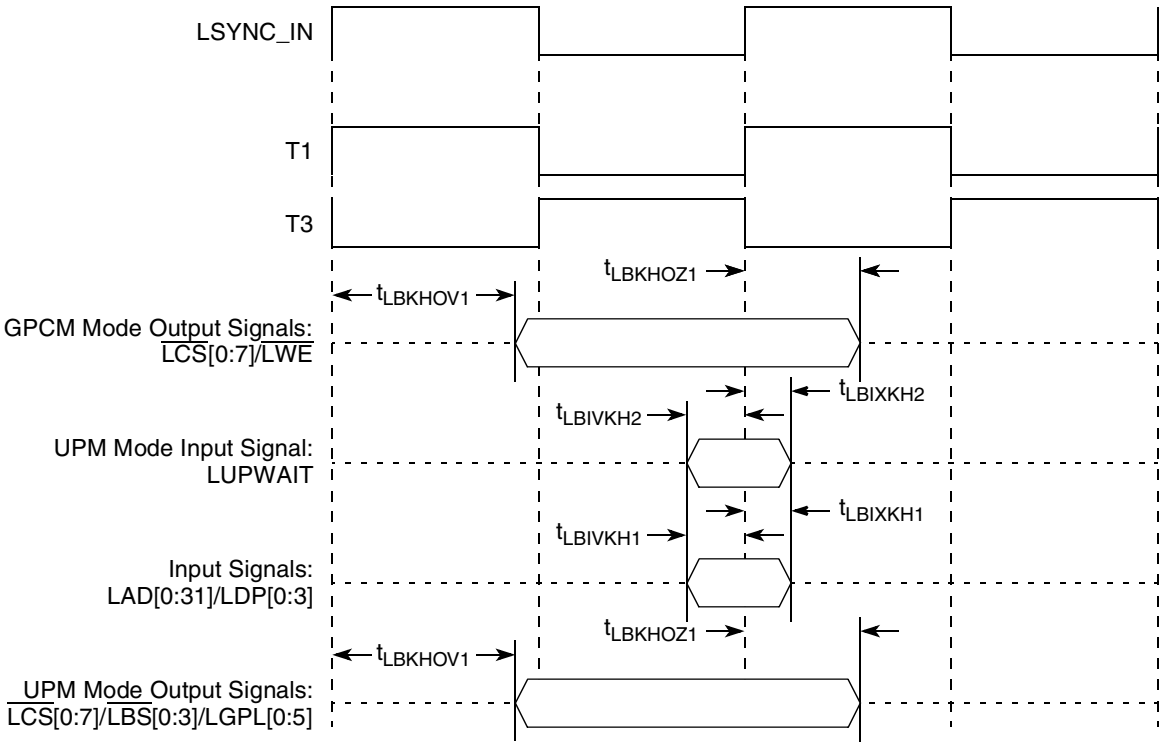

Figure 19. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

11 JTAG

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8555E.

Table 38 provides the JTAG AC timing specifications as defined in Figure 33 through Figure 36.

Table 38. JTAG AC Timing Specifications (Independent of SYSCLK) [1]

At recommended operating conditions (see Table 2).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	
JTAG external clock cycle time	t_{JTG}	30	—	ns	
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 0	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 20 25	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 4 4	 20 25	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 — —	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 3 3	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 32). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design.

Figure 32 provides the AC test load for TDO and the boundary-scan outputs of the MPC8555E.

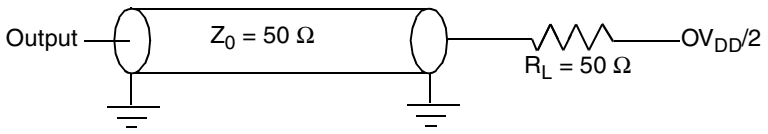

Figure 32. AC Test Load for the JTAG Interface

Figure 33 provides the JTAG clock input timing diagram.

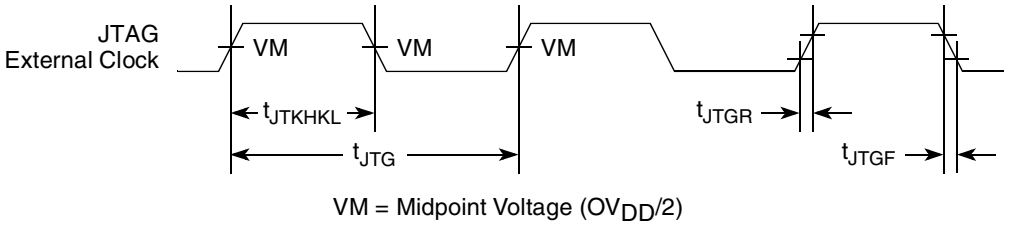

Figure 33. JTAG Clock Input Timing Diagram

Figure 34 provides the $\overline{\text{TRST}}$ timing diagram.

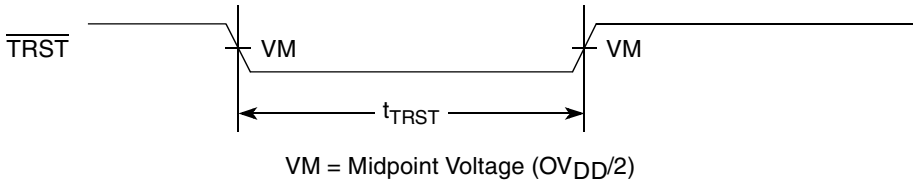

Figure 34. $\overline{\text{TRST}}$ Timing Diagram

Figure 35 provides the boundary-scan timing diagram.

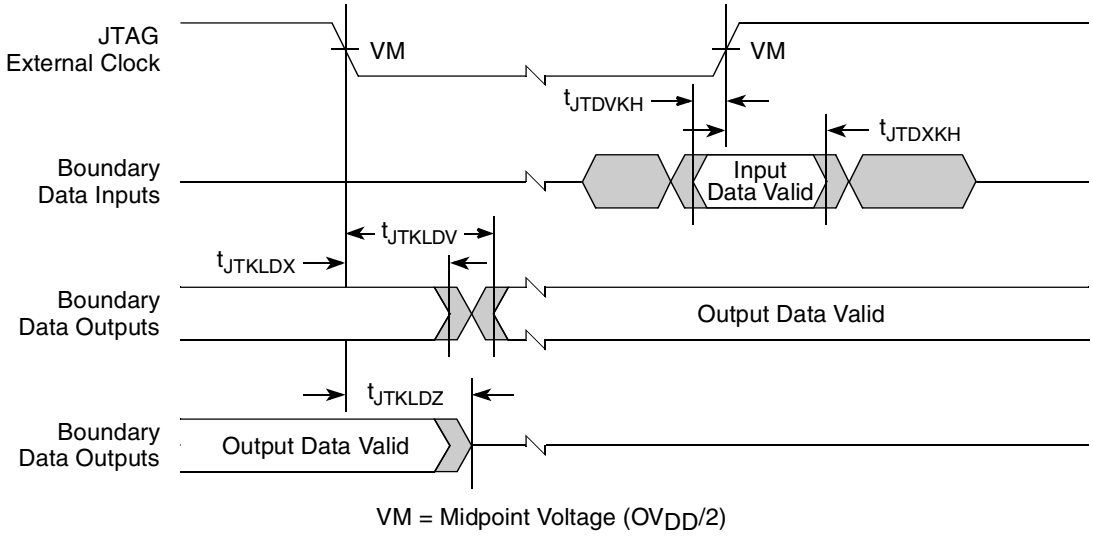

Figure 35. Boundary-Scan Timing Diagram

Table 43. MPC8555E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LA[28:31]	T18, T19, T20, T21	O	OV_{DD}	5, 7, 9
LAD[0:31]	AD26, AD27, AD28, AC26, AC27, AC28, AA22, AA23, AA26, Y21, Y22, Y26, W20, W22, W26, V19, T22, R24, R23, R22, R21, R18, P26, P25, P20, P19, P18, N22, N23, N24, N25, N26	I/O	OV_{DD}	—
LALE	V21	O	OV_{DD}	5, 8, 9
LBCTL	V20	O	OV_{DD}	9
LCKE	U23	O	OV_{DD}	—
LCLK[0:2]	U27, U28, V18	O	OV_{DD}	—
$\overline{\text{LCS}}$[0:4]	Y27, Y28, W27, W28, R27	O	OV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	R28	I/O	OV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	P27	O	OV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	P28	O	OV_{DD}	1
LDP[0:3]	AA27, AA28, T26, P21	I/O	OV_{DD}	—
LGPL0/LSDA10	U19	O	OV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	U22	O	OV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	V28	O	OV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	V27	O	OV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/ LPBSE	V23	I/O	OV_{DD}	21
LGPL5	V22	O	OV_{DD}	5, 9
LSYNC_IN	T27	I	OV_{DD}	—
LSYNC_OUT	T28	O	OV_{DD}	—
$\overline{\text{LWE}}$[0:1]/LSDDQM[0:1]/ $\overline{\text{LBS}}$[0:1]	AB28, AB27	O	OV_{DD}	1, 5, 9
$\overline{\text{LWE}}$[2:3]/LSDDQM[2:3]/ $\overline{\text{LBS}}$[2:3]	T23, P24	O	OV_{DD}	1, 5, 9
DMA				
$\overline{\text{DMA\_DREQ}}$[0:1]	H5, G4	I	OV_{DD}	—
$\overline{\text{DMA\_DACK}}$[0:1]	H6, G5	O	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	H7, G6	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{MCP}}$	AG17	I	OV_{DD}	—
$\overline{\text{UDE}}$	AG16	I	OV_{DD}	—

Table 43. MPC8555E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
JTAG				
TCK	AF21	I	OV_{DD}	—
TDI	AG21	I	OV_{DD}	12
TDO	AF19	O	OV_{DD}	11
TMS	AF23	I	OV_{DD}	12
$\overline{\text{TRST}}$	AG23	I	OV_{DD}	12
DFT				
$\overline{\text{LSSD\_MODE}}$	AG19	I	OV_{DD}	20
L1_TSTCLK	AB22	I	OV_{DD}	20
L2_TSTCLK	AG22	I	OV_{DD}	20
$\overline{\text{TEST\_SEL0}}$	AH20	I	OV_{DD}	3
TEST_SEL1	AG26	I	OV_{DD}	3
Thermal Management				
THERM0	AG2	—	—	14
THERM1	AH3	—	—	14
Power Management				
ASLEEP	AG18	—	—	9, 18
Power and Ground Signals				
$AV_{DD}1$	AH19	Power for e500 PLL (1.2 V)	$AV_{DD}1$	—
$AV_{DD}2$	AH18	Power for CCB PLL (1.2 V)	$AV_{DD}2$	—
$AV_{DD}3$	AH17	Power for CPM PLL (1.2 V)	$AV_{DD}3$	—
$AV_{DD}4$	AF28	Power for PCI1 PLL (1.2 V)	$AV_{DD}4$	—
$AV_{DD}5$	AE28	Power for PCI2 PLL (1.2 V)	$AV_{DD}5$	—

15.2 Platform/System PLL Ratio

The platform clock is the clock that drives the L2 cache, the DDR SDRAM data rate, and the e500 core complex bus (CCB), and is also called the CCB clock. The values are determined by the binary value on LA[28:31] at power up, as shown in Table 46.

There is no default for this PLL ratio; these signals must be pulled to the desired values.

For specifications on the PCI_CLK, refer to the PCI 2.2 Specification.

Table 46. CCB Clock Ratio

Binary Value of LA[28:31] Signals	Ratio Description
0000	16:1 ratio CCB clock: SYSCLK (PCI bus)
0001	Reserved
0010	2:1 ratio CCB clock: SYSCLK (PCI bus)
0011	3:1 ratio CCB clock: SYSCLK (PCI bus)
0100	4:1 ratio CCB clock: SYSCLK (PCI bus)
0101	5:1 ratio CCB clock: SYSCLK (PCI bus)
0110	6:1 ratio CCB clock: SYSCLK (PCI bus)
0111	Reserved
1000	8:1 ratio CCB clock: SYSCLK (PCI bus)
1001	9:1 ratio CCB clock: SYSCLK (PCI bus)
1010	10:1 ratio CCB clock: SYSCLK (PCI bus)
1011	Reserved
1100	12:1 ratio CCB clock: SYSCLK (PCI bus)
1101	Reserved
1110	Reserved
1111	Reserved

Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that allows the MPC8555E to function in various environments.

16.2.1 Recommended Thermal Model

For system thermal modeling, the MPC8555E thermal model is shown in Figure 44. Five cuboids are used to represent this device. To simplify the model, the solder balls and substrate are modeled as a single block 29x29x1.6 mm with the conductivity adjusted accordingly. The die is modeled as 8.7 x 9.3 mm at a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed resistance between the die and substrate assuming a conductivity of 4.4 W/m•K in the thickness dimension of 0.07 mm. The lid attach adhesive is also modeled as a collapsed resistance with dimensions of 8.7 x 9.3 x 0.05 mm and the conductivity of 1.07 W/m•K. The nickel plated copper lid is modeled as 11 x 11 x 1 mm.

Conductivity	Value	Unit
Lid ($11 \times 11 \times 1$ mm)		
k_x	360	W/(m × K)
k_y	360	
k_z	360	
Lid Adhesive—Collapsed resistance ($8.7 \times 9.3 \times 0.05$ mm)		
k_z	1.07	
Die ($8.7 \times 9.3 \times 0.75$ mm)		
Bump/Underfill—Collapsed resistance ($8.7 \times 9.3 \times 0.07$ mm)		
k_z	4.4	
Substrate and Solder Balls ($25 \times 25 \times 1.6$ mm)		
k_x	14.2	
k_y	14.2	
k_z	1.2	

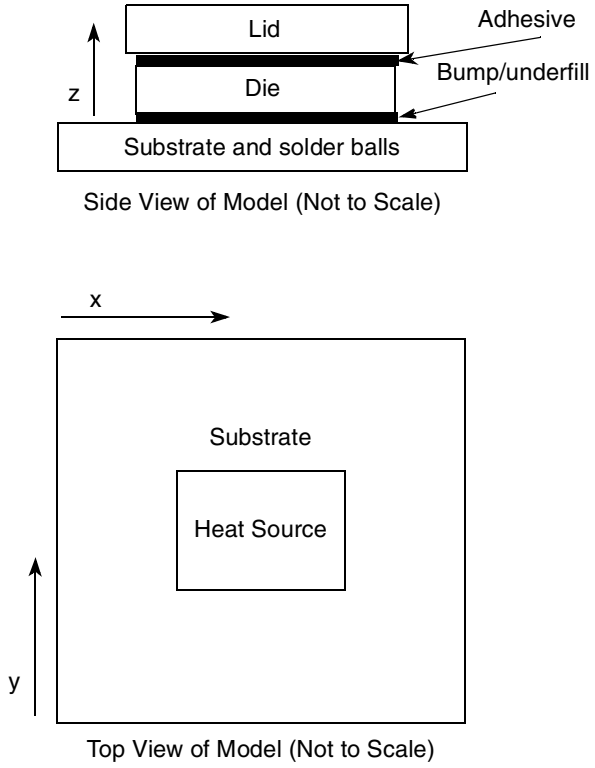

Figure 44. MPC8555E Thermal Model

Chanhassen, MN 55317
Internet: www.bergquistcompany.com

Thermagon Inc. 888-246-9050
4707 Detroit Ave.
Cleveland, OH 44102
Internet: www.thermagon.com

16.2.4 Heat Sink Selection Examples

The following section provides a heat sink selection example using one of the commercially available heat sinks.

16.2.4.1 Case 1

For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

$$T_J = T_I + T_R + (\theta_{JC} + \theta_{INT} + \theta_{SA}) \times P_D$$

where

T_J is the die-junction temperature

T_I is the inlet cabinet ambient temperature

T_R is the air temperature rise within the computer cabinet

θ_{JC} is the junction-to-case thermal resistance

θ_{INT} is the adhesive or interface material thermal resistance

θ_{SA} is the heat sink base-to-ambient thermal resistance

P_D is the power dissipated by the device. See Table 4 and Table 5.

During operation the die-junction temperatures (T_J) should be maintained within the range specified in Table 2. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_A) may range from 30° to 40°C. The air temperature rise within a cabinet (T_R) may be in the range of 5° to 10°C. The thermal resistance of some thermal interface material (θ_{INT}) may be about 1°C/W. For the purposes of this example, the θ_{JC} value given in Table 49 that includes the thermal grease interface and is documented in note 4 is used. If a thermal pad is used, θ_{INT} must be added.

Assuming a T_I of 30°C, a T_R of 5°C, a FC-PBGA package θ_{JC} = 0.96, and a power consumption (P_D) of 8.0 W, the following expression for T_J is obtained:

$$\text{Die-junction temperature: } T_J = 30°C + 5°C + (0.96°C/W + \theta_{SA}) \times 8.0\ W$$

The heat sink-to-ambient thermal resistance (θ_{SA}) versus airflow velocity for a Thermalloy heat sink #2328B is shown in Figure 47.

Assuming an air velocity of 2 m/s, we have an effective θ_{SA+} of about 3.3°C/W, thus

$$T_J = 30°C + 5°C + (0.96°C/W + 3.3°C/W) \times 8.0\ W,$$

resulting in a die-junction temperature of approximately 69°C which is well within the maximum operating temperature of the component.

17.8.1 Termination of Unused Signals

If the JTAG interface and COP header are not used, Freescale recommends the following connections:

- $\overline{\text{TRST}}$ should be tied to $\overline{\text{HRESET}}$ through a 0 kΩ isolation resistor so that it is asserted when the system reset signal ($\overline{\text{HRESET}}$) is asserted, ensuring that the JTAG scan chain is initialized during the power-on reset flow. Freescale recommends that the COP header be designed into the system as shown in Figure 53. If this is not possible, the isolation resistor allows future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.
- Tie TCK to OV_{DD} through a 10 kΩ resistor. This prevents TCK from changing state and reading incorrect data into the device.
- No connection is required for TDI, TMS, or TDO.